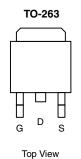


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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

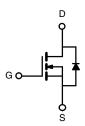
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0041			
I <sub>D</sub> (A)	50			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified<sup>d</sup>
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





N-Channel MOSFET

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM50N04-4m1-GE3		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	40	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Dunin Comments	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	50		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 125 °C		50		
Continuous Source Current (Diode Conduc	I <sub>S</sub>	50	Α		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	200			
Single Pulse Avalanche Current		I <sub>AS</sub>	60		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	180	mJ	
Maximum Dawar Dissipationh	T <sub>C</sub> = 25 °C	D	150	\A/	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	50	W	
Operating Junction and Storage Temperatu	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1	- C/VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				l	•	ı	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	50	μΑ
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	250	-
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.0030	0.0041	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.0068	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.0082	
Forward Transconductanceb	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		-	200	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	5372	6715	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{GS} = 0 V$ $V_{DS} = 25 V$ , $f = 1 MHz$		512	640	рF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	256	320	
Total Gate Charge <sup>c</sup>	Qg			-	70	105	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$	-	16	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	12.6	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz		1.86	2.8	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				12	18	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V, } R_L = 0.4 \Omega$ $I_D \cong 50 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	5	8	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	35	53	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	9	14	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>	•			•		
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0 V		-	0.86	1.5	V

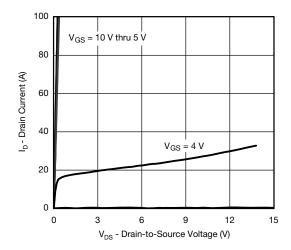
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

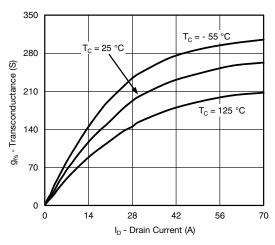
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



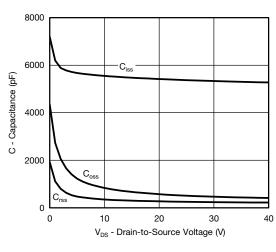
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



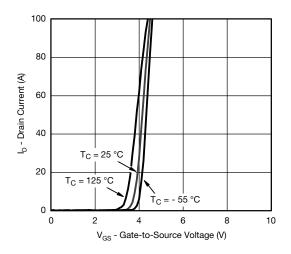
## **Output Characteristics**



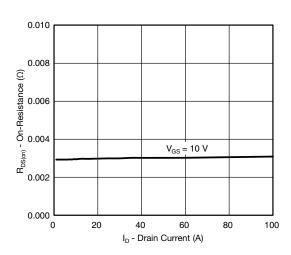
## Transconductance



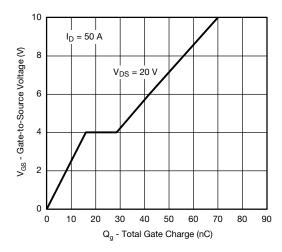
Capacitance



## **Transfer Characteristics**



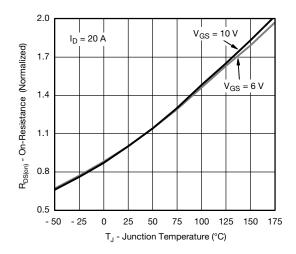
On-Resistance vs. Drain Current



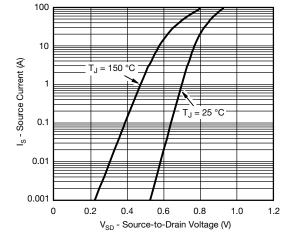
Gate Charge



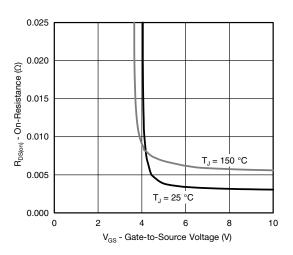
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



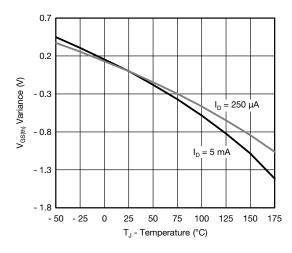
#### On-Resistance vs. Junction Temperature



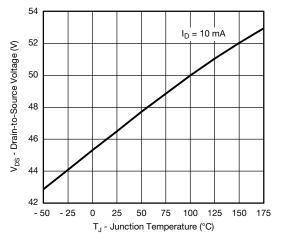
## **Source Drain Diode Forward Voltage**



On-Resistance vs. Gate-to-Source Voltage



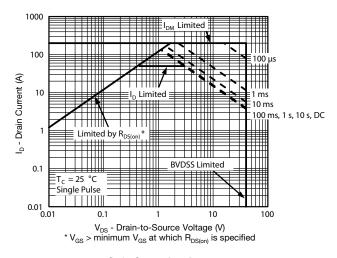
Threshold Voltage



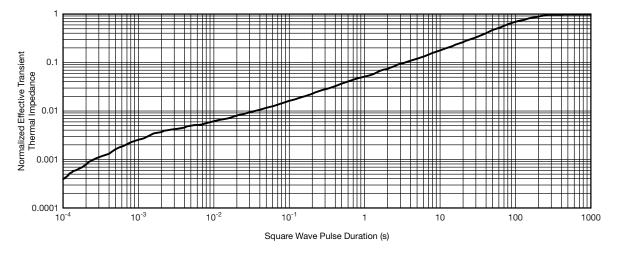
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



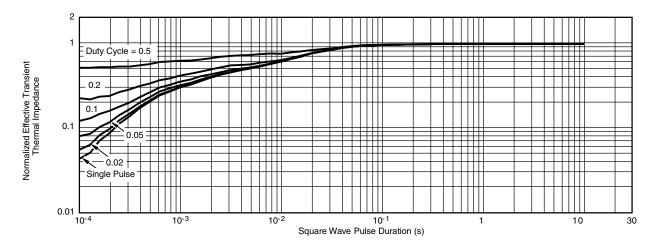
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

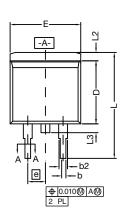
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

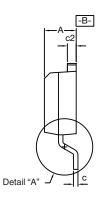
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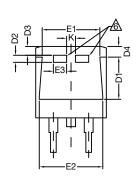


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# TO-263 (D<sup>2</sup>PAK): 3-LEAD

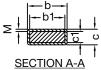








**DETAIL A (ROTATED 90°)** 



1			1
≥⊹	<i>7777777</i>	붓	
ı	WHITE OF THE PARTY	1	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

	INCHES		MILLIN	METERS	
	DIM.	MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	BSC	2.54 BSC	
	K	0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
	М	-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					

DWG: 5843

Revison: 30-Sep-13 Document Number: 71198





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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